

## Power MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	- 200	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = - 10$ V	1.5
$Q_g$ (Max.) (nC)	22	
$Q_{gs}$ (nC)	12	
$Q_{gd}$ (nC)	10	
Configuration	Single	

### FEATURES

- Dynamic  $dV/dt$  Rating
- P-Channel
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC



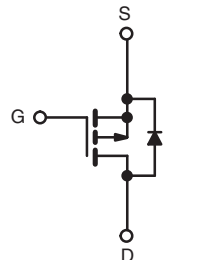
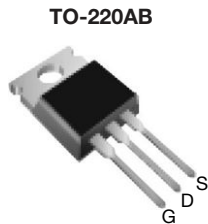
Available

**RoHS\***  
 COMPLIANT

### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.



P-Channel MOSFET

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	IRF9620PbF
	SiHF9620-E3
SnPb	IRF9620
	SiHF9620

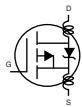
ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL		LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$		- 200	V
Gate-Source Voltage	$V_{GS}$		$\pm 20$	
Continuous Drain Current	$V_{GS}$ at - 10 V	$T_C = 25$ °C	- 3.5	A
		$T_C = 100$ °C	- 2.0	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$		- 14	
Linear Derating Factor			0.32	W/°C
Maximum Power Dissipation	$T_C = 25$ °C		40	W
Peak Diode Recovery $dV/dt^b$	$dV/dt$		- 5.0	V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$		- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s		300 <sup>c</sup>	
Mounting Torque	6-32 or M3 screw		10	
			1.1	N · m

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $I_{SD} \leq - 3.5$  A,  $dI/dt \leq 95$  A/ $\mu$ s,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150$  °C.
- 1.6 mm from case.

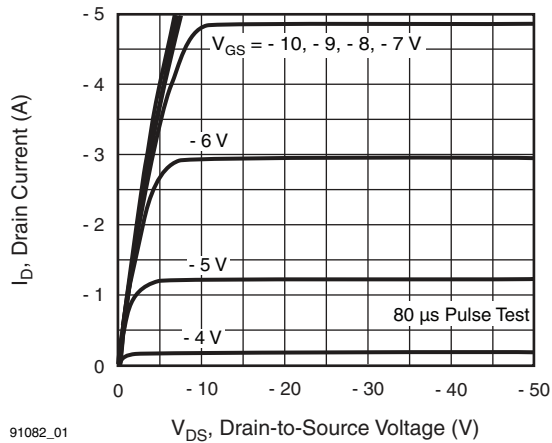
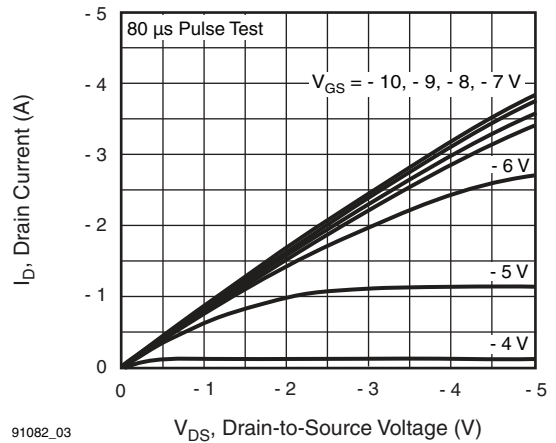
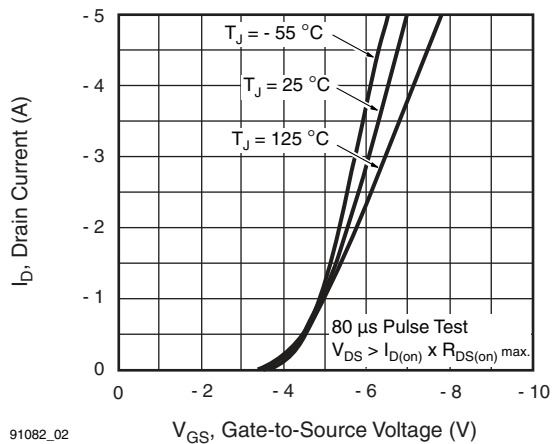
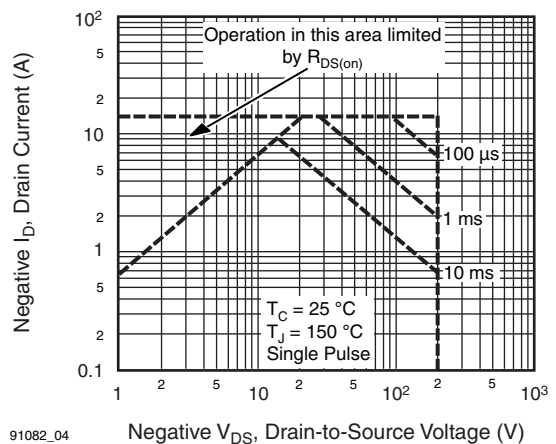
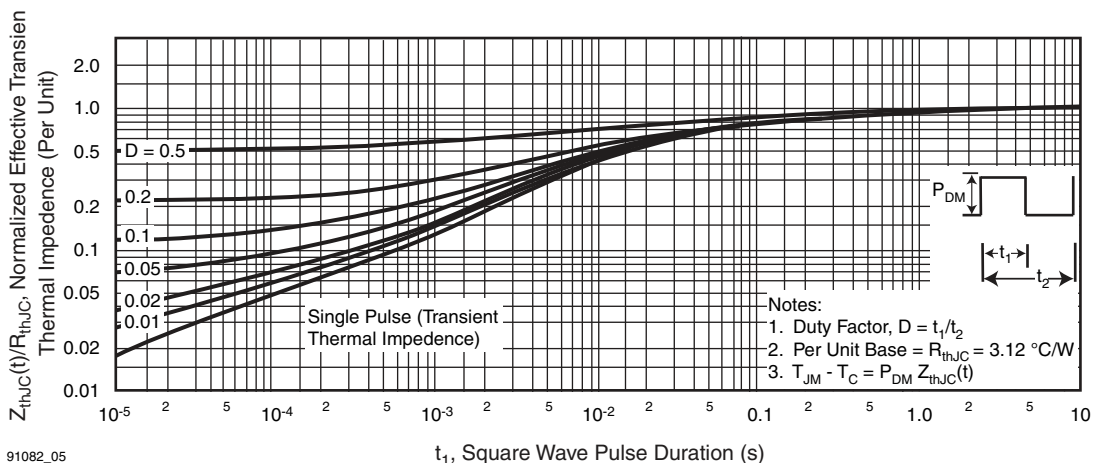
\* Pb containing terminations are not RoHS compliant, exemptions may apply

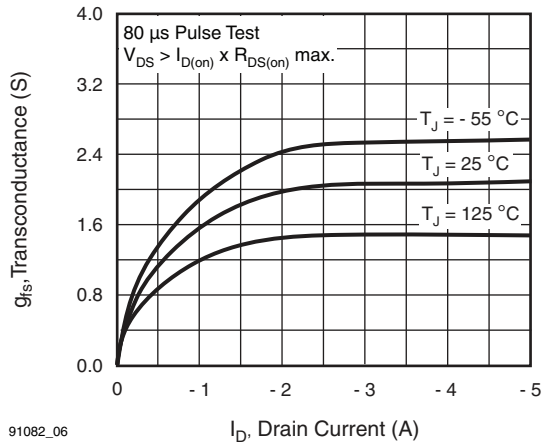
THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	$R_{thCS}$	0.50	-	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	3.1	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = -250\text{ }\mu\text{A}$	-200	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = -1\text{ mA}$	-	-0.22	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250\text{ }\mu\text{A}$	-2.0	-	-4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -200\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	-100	$\mu\text{A}$
		$V_{DS} = -160\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$	-	-	-500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$ , $I_D = -1.5\text{ A}^b$	-	-	1.5	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = -50\text{ V}$ , $I_D = -1.5\text{ A}^b$	1.0	-	-	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = -25\text{ V}$ , $f = 1.0\text{ MHz}$ , see fig. 5	-	350	-	pF
Output Capacitance	$C_{oss}$		-	100	-	
Reverse Transfer Capacitance	$C_{rss}$		-	30	-	
Total Gate Charge	$Q_g$	$V_{GS} = -10\text{ V}$ , $I_D = -4.0\text{ A}$ , $V_{DS} = -160\text{ V}$ , see fig. 11 and 18 <sup>b</sup>	-	-	22	nC
Gate-Source Charge	$Q_{gs}$		-	-	12	
Gate-Drain Charge	$Q_{gd}$		-	-	10	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -100\text{ V}$ , $I_D = -1.5\text{ A}$ , $R_g = 50\text{ }\Omega$ , $R_D = 67\text{ }\Omega$ , see fig. 17 <sup>b</sup>	-	15	-	ns
Rise Time	$t_r$		-	25	-	
Turn-Off Delay Time	$t_{d(off)}$		-	20	-	
Fall Time	$t_f$		-	15	-	
Internal Drain Inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact	-	4.5	-	nH
Internal Source Inductance	$L_S$		-	7.5	-	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode	-	-	-3.5	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$		-	-	-14	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_S = -3.5\text{ A}$ , $V_{GS} = 0\text{ V}^b$	-	-	-7.0	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_F = -3.5\text{ A}$ , $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	300	450	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	1.9	2.9	$\mu\text{C}$
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )				

### Notes

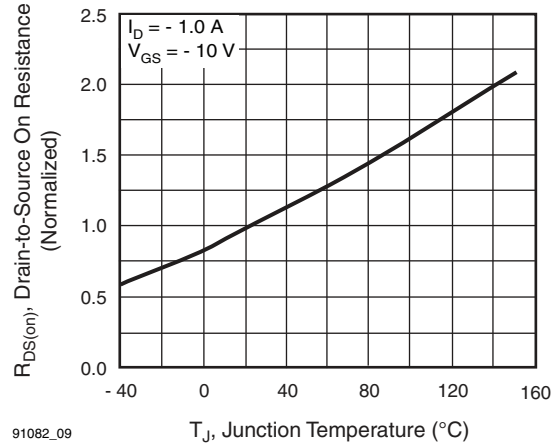
- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 3 - Typical Saturation Characteristics**

**Fig. 2 - Typical Transfer Characteristics**

**Fig. 4 - Maximum Safe Operating Area**

**Fig. 5 - Maximum Effective Transient Thermal Impedance, Junction-to-Case vs. Pulse Duration**



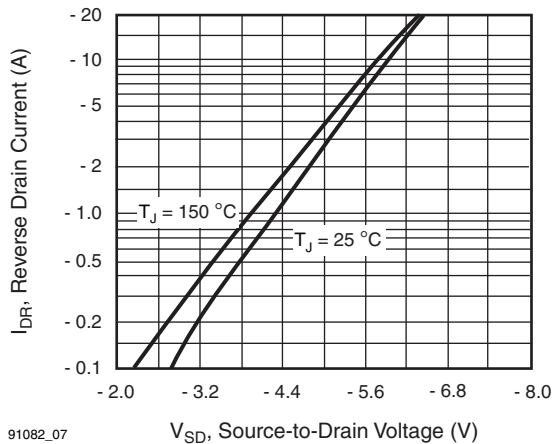
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**Fig. 6 - Typical Transconductance vs. Drain Current**



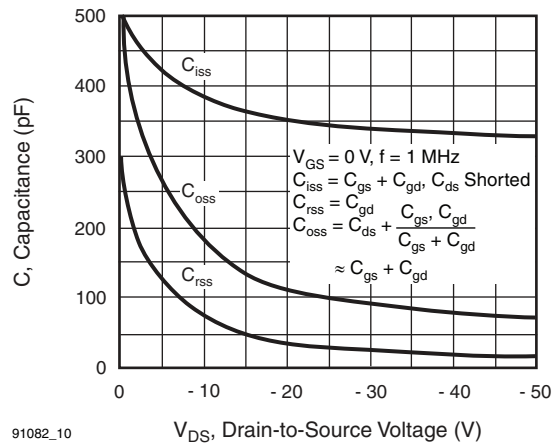
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**Fig. 9 - Normalized On-Resistance vs. Temperature**



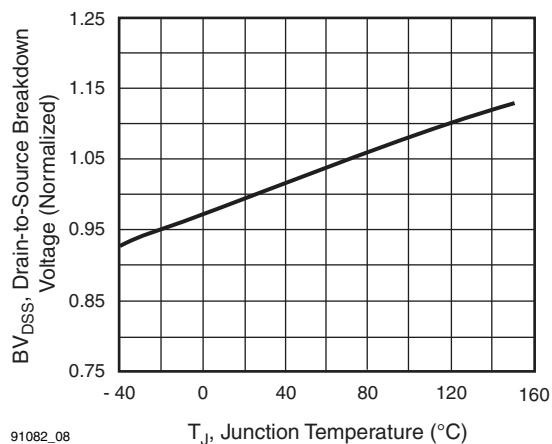
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**Fig. 7 - Typical Source-Drain Diode Forward Voltage**



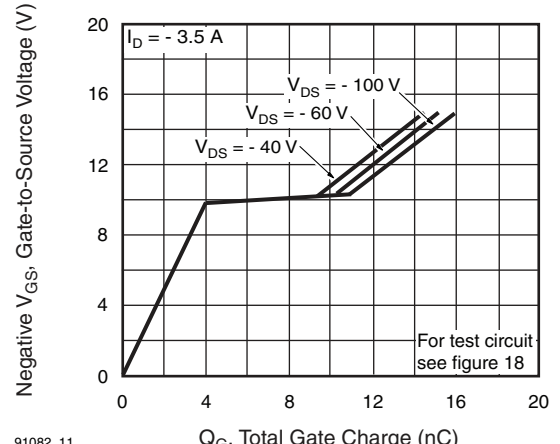
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**Fig. 10 - Typical Capacitance vs. Drain-to-Source Voltage**



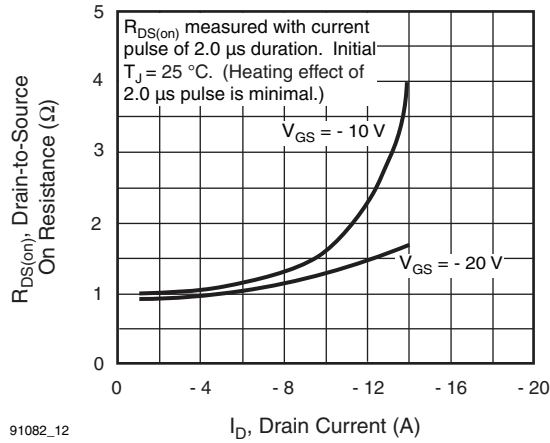
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**Fig. 8 - Breakdown Voltage vs. Temperature**



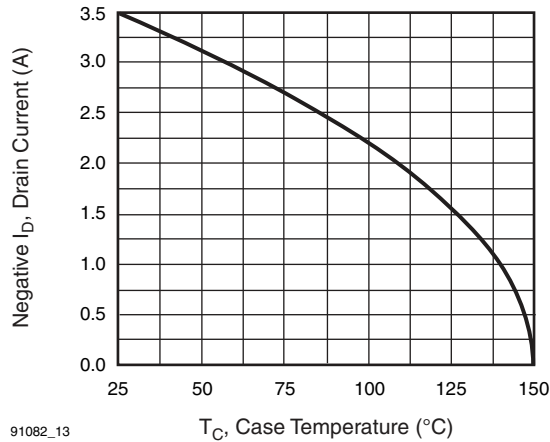
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**Fig. 11 - Typical Gate Charge vs. Gate-to-Source Voltage**



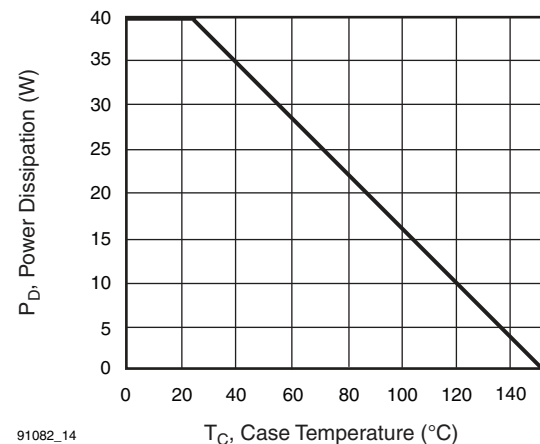
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**Fig. 12 - Typical On-Resistance vs. Drain Current**



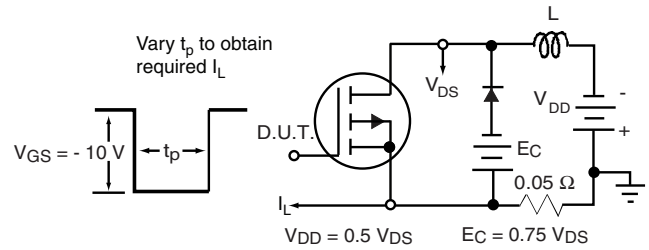
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**Fig. 13 - Maximum Drain Current vs. Case Temperature**

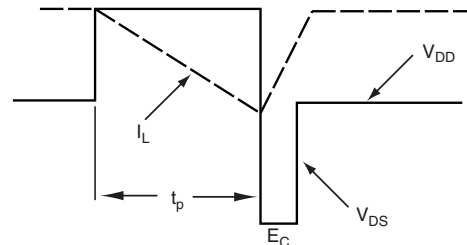


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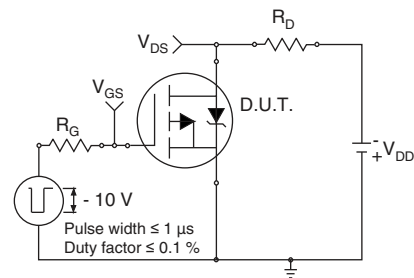
**Fig. 14 - Power vs. Temperature Derating Curve**



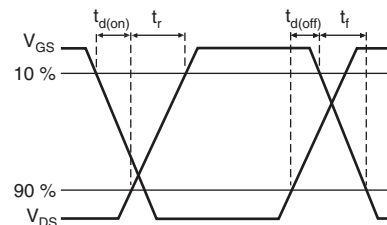
**Fig. 15 - Clamped Inductive Test Circuit**



**Fig. 16 - Clamped Inductive Waveforms**



**Fig. 17a - Switching Time Test Circuit**



**Fig. 17b - Switching Time Waveforms**

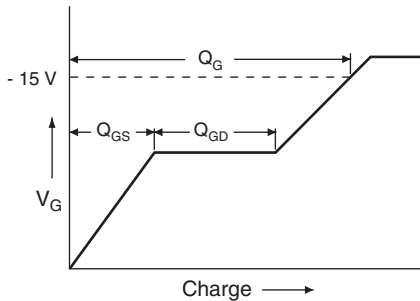


Fig. 18a - Basic Gate Charge Waveform

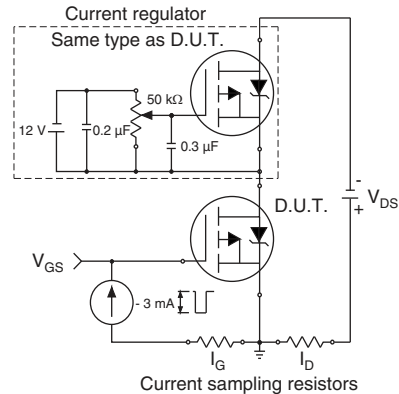


Fig. 18b - Gate Charge Test Circuit

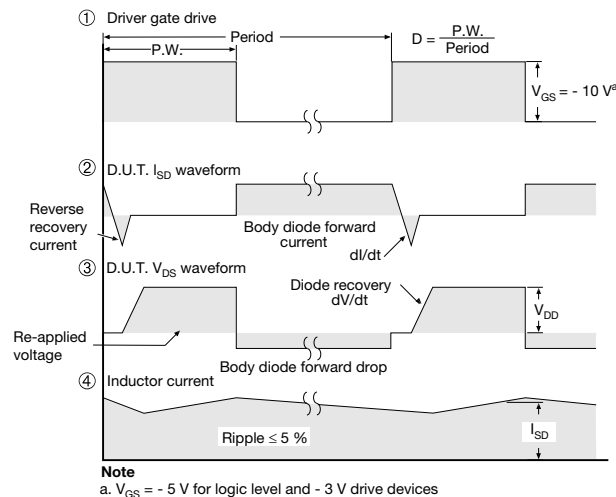
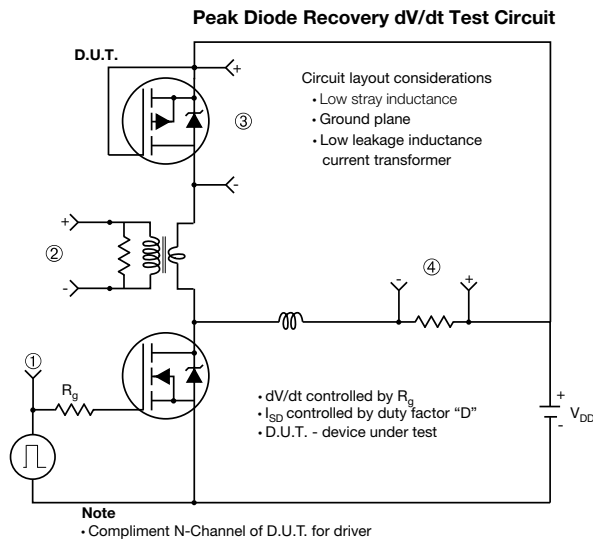


Fig. 19 - For P-Channel

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## TO-220-1



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15  
DWG: 6031

**Note**

- M\* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM





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